

SFH 7051



Features:

- Multi chip package featuring 3 green emitters and one detector
- Small package:
(WxDxH) 4.7 mm x 2.5 mm x 0.9 mm
- Light Barrier to block optical crosstalk

Applications

- Heart rate monitoring

for:

- Wearable devices (e.g. smart watches, fitness trackers, ...)
- Mobile devices

Besondere Merkmale:

- Multi-Chip-Gehäuse mit 3 grünen Emittern und einem Detektor
- Kleines Gehäuse:
(BxTxH) 4.7 mm x 2.5 mm x 0.9 mm
- Lichtsperre zur Unterdrückung von optischem Übersprechen

Anwendungen

- Herzfrequenzüberwachung

für:

- Tragbare Geräte (z.B. Smart watches, Fitness tracker, ...)
- Mobile Geräte

Ordering Information SFH 7051

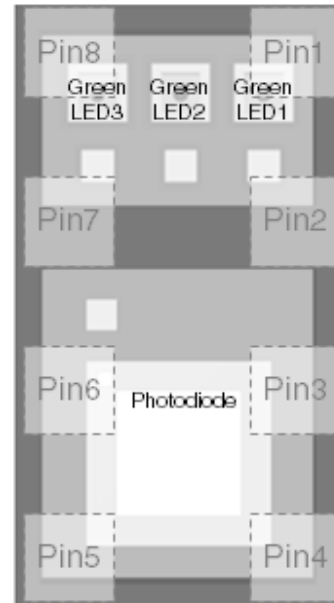
Bestellinformation

Type	Ordering Code
Typ	Bestellnummer
SFH 7051	Q65111A7792

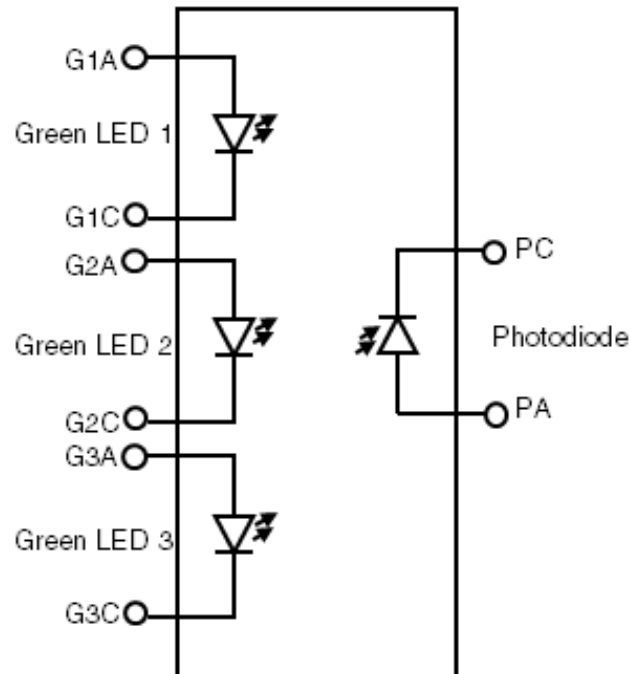
Pin configuration

Pin	Name	Function
1	G1A	Green LED Anode
2	G1C	Green LED Cathode
3	G2C	Green LED Cathode
4	PA	Photodiode Anode
5	PC	Photodiode Cathode
6	G2A	Green LED Anode
7	G3C	Green LED Cathode
8	G3A	Green LED Anode

Top view



Block diagram



Maximum Ratings ($T_A = 25\text{ °C}$)

Parameter	Symbol	Values	Unit
General			
Operating temperature range	T_{op}	-40 ... 85	°C
Storage temperature range	T_{stg}	-40 ... 85	°C
ESD withstand voltage (acc. to ANSI/ ESDA/ JEDEC JS-001 - HBM)	V_{ESD}	2	kV
Green Emitters			
Reverse voltage	V_R	5	V
Forward current (single emitter operation)	$I_{F(DC)}$	25	mA
Forward current (all emitters active)	$I_{F(DC)}$	15	mA
Surge current ($t_p = 100\text{ }\mu\text{s}$, $D = 0$)	I_{FSM}	300	mA
Detector			
Reverse voltage ($I_R = 100\text{ }\mu\text{A}$, $E_e = 0\text{ mW/cm}^2$)	V_R	16	V

Characteristics ($T_A = 25\text{ °C}$)

Parameter		Symbol	Value	Unit
Green Emitter (single emitter)				
Wavelength of peak emission ($I_F = 20\text{ mA}$)	(typ.)	λ_{peak}	530	nm
Centroid Wavelength ($I_F = 20\text{ mA}$)	(typ. (max.))	$\lambda_{\text{centroid}}$	535 (± 10)	nm
Spectral bandwidth at 50% of I_{max} ($I_F = 20\text{ mA}$)	(typ.)	$\Delta\lambda$	34	nm
Half angle	(typ.)	φ	± 60	°
Rise and fall time of I_e (10% and 90% of $I_{e,\text{max}}$) ($I_F = 100\text{ mA}$, $t_p = 16\text{ }\mu\text{s}$, $R_L = 50\text{ }\Omega$)	(typ.)	t_r, t_f	32	ns
Forward voltage ($I_F = 20\text{ mA}$)	(typ. (max.))	V_F	3.2 (≤ 3.7)	V
Reverse current ($V_R = 5\text{ V}$)		I_R	not designed for reverse operation	μA
Radiant intensity ($I_F = 20\text{ mA}$, $t_p = 20\text{ ms}$)	(typ.)	I_e	1.4	mW / sr
Total radiant flux ($I_F = 20\text{ mA}$, $t_p = 20\text{ ms}$)	(typ.)	Φ_e	3.4	mW
Temperature coefficient of $\lambda_{\text{centroid}}$ ($I_F = 20\text{ mA}$, $-10\text{ °C} \leq T \leq 100\text{ °C}$)	(typ.)	$\text{TC}_{\lambda_{\text{centroid}}}$	0.02	nm / K
Temperature coefficient of V_F ($I_F = 20\text{ mA}$, $-10\text{ °C} \leq T \leq 100\text{ °C}$)	(typ.)	TC_V	-4.0	mV / K

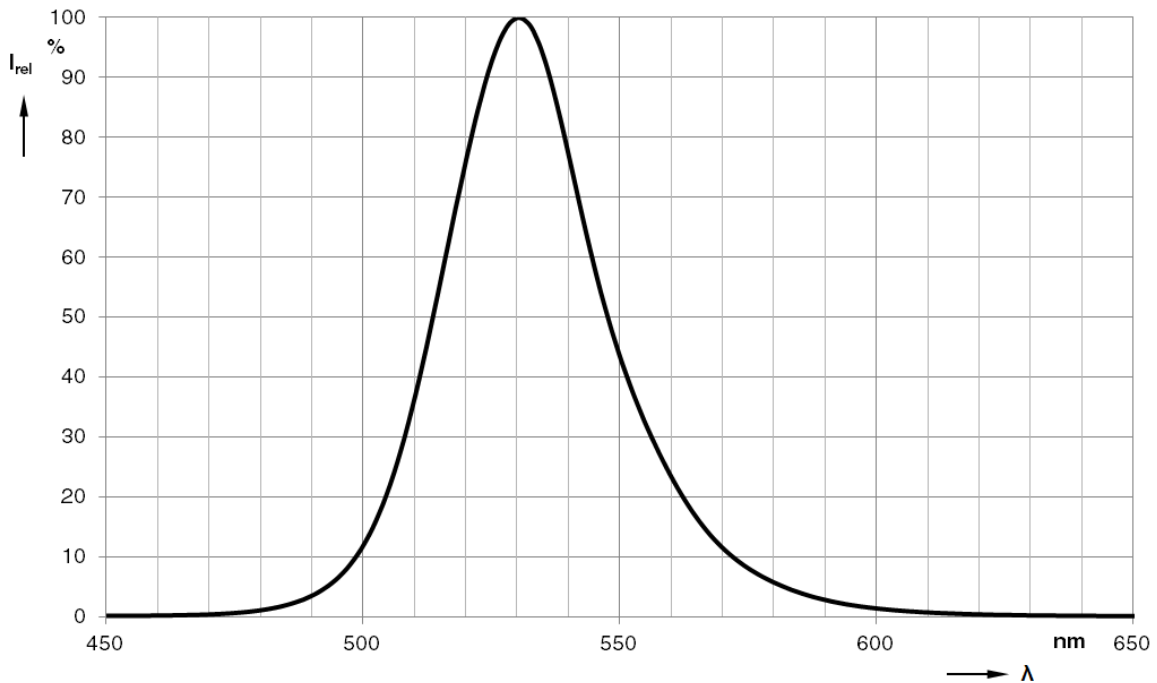
Characteristics ($T_A = 25\text{ °C}$)

Parameter		Symbol	Value	Unit
Detector				
Photocurrent ($E_e = 0.1\text{ mW/cm}^2$, $\lambda = 535\text{ nm}$, $V_R = 5\text{ V}$)	(typ.)	$I_{P,535}$	0.42	μA
Wavelength of max. sensitivity	(typ.)	$\lambda_{S\text{ max}}$	920	nm
Spectral range of sensitivity	(typ.)	$\lambda_{10\%}$	400 ... 1100	nm
Radiation sensitive area	(typ.)	A	1.7	mm^2
Dimensions of radiant sensitive area	(typ.)	L x W	1.3 x 1.3	mm x mm
Dark current ($V_R = 5\text{ V}$, $E_e = 0\text{ mW/cm}^2$)	(typ. (max.))	I_R	1 (≤ 5)	nA
Spectral sensitivity of the chip ($\lambda = 535\text{ nm}$)	(typ.)	$S_{\lambda,535}$	0.27	A / W
Open-circuit voltage ($E_e = 0.1\text{ mW/cm}^2$, $\lambda = 535\text{ nm}$)	(typ.)	$V_{O,535}$	240	mV
Short-circuit current ($E_e = 0.1\text{ mW/cm}^2$, $\lambda = 535\text{ nm}$)	(typ.)	$I_{SC,535}$	0.40	μA
Rise and fall time ($V_R = 3.3\text{ V}$, $R_L = 50\ \Omega$, $\lambda = 535\text{ nm}$)	(typ.)	t_r, t_f	42	ns
Forward voltage ($I_F = 10\text{ mA}$, $E = 0\text{ mW/cm}^2$)	(typ.)	V_F	0.9	V
Capacitance ($V_R = 5\text{ V}$, $f = 1\text{ MHz}$, $E = 0\text{ mW/cm}^2$)	(typ.)	C_0	5	pF

Diagrams for green emitters

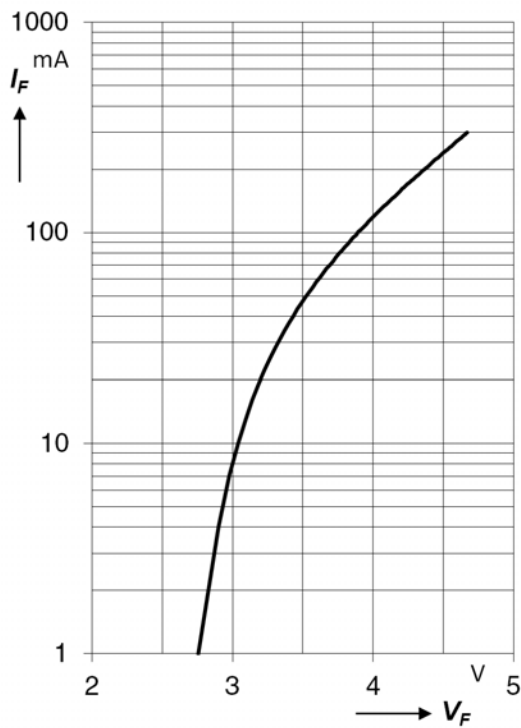
Relative spectral emission ¹⁾

$I_{rel} = f(\lambda), T_A = 25\text{ }^\circ\text{C}, I_F = 20\text{ mA}$



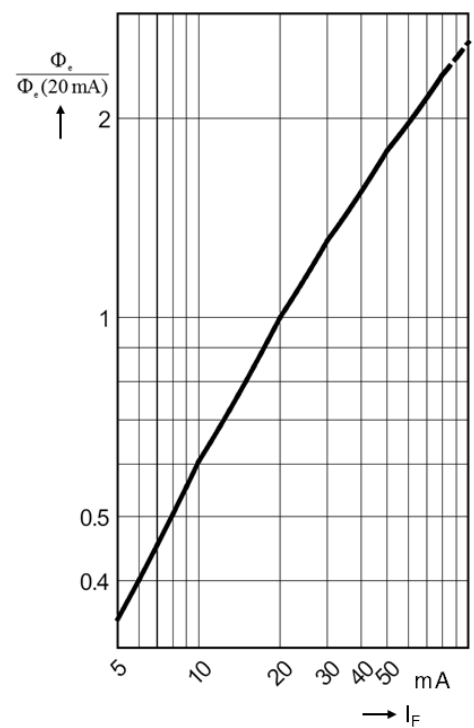
Forward current ¹⁾

$I_F = f(V_F), T_A = 25\text{ }^\circ\text{C}$



Relative radiant flux ¹⁾

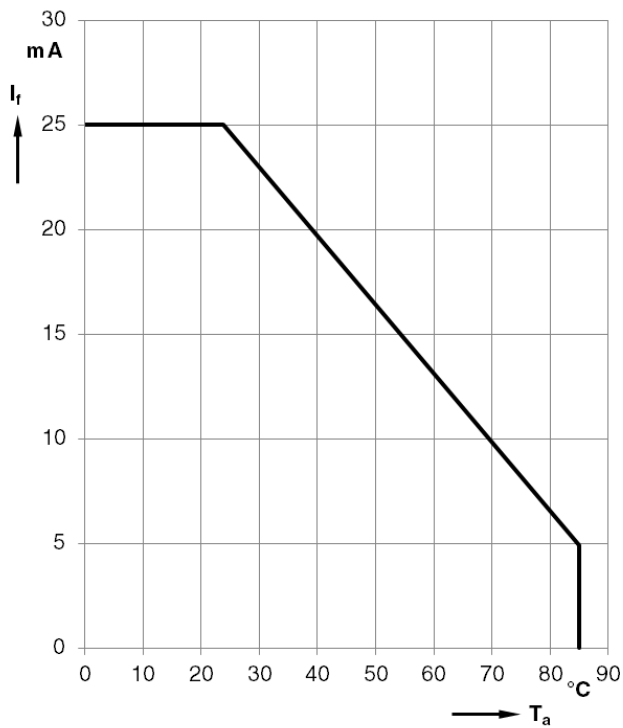
$\Phi_e / \Phi_e(20\text{ mA}) = f(I_F), \text{ single pulse, } t_p = 25\mu\text{s}, T_A = 25\text{ }^\circ\text{C}$



Diagrams for green emitters

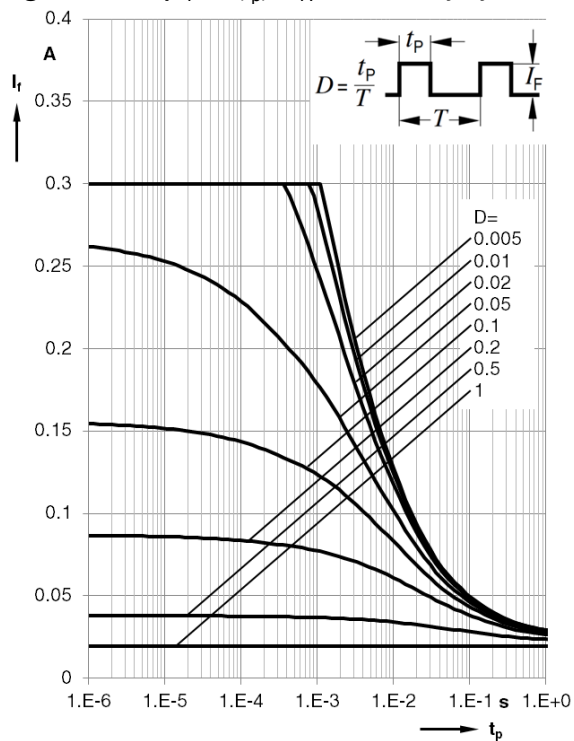
Max. permissible forward current ¹⁾

(single emitter) $I_{F,max} = f(T_A)$, $R_{thJA} = 800 \text{ K/W}$



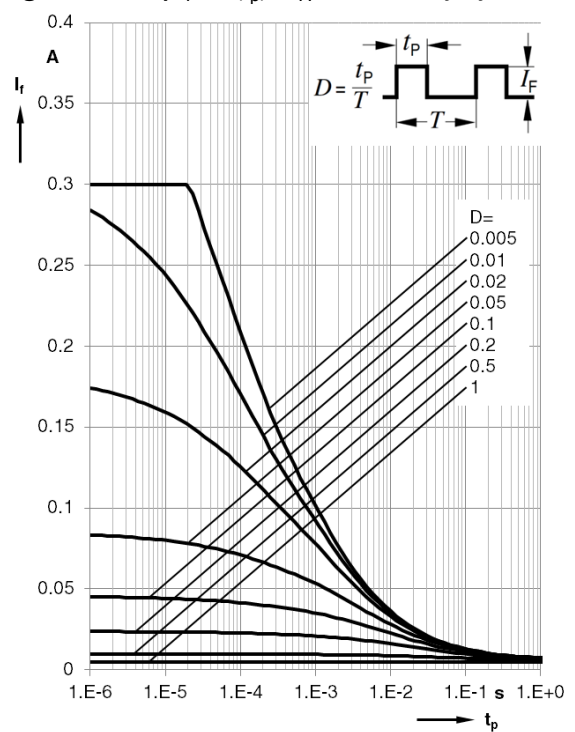
Permissible pulse handling capability ¹⁾

(single emitter) $I_F = f(t_p)$, $T_A = 40^\circ\text{C}$, duty cycle D



Permissible pulse handling capability ¹⁾

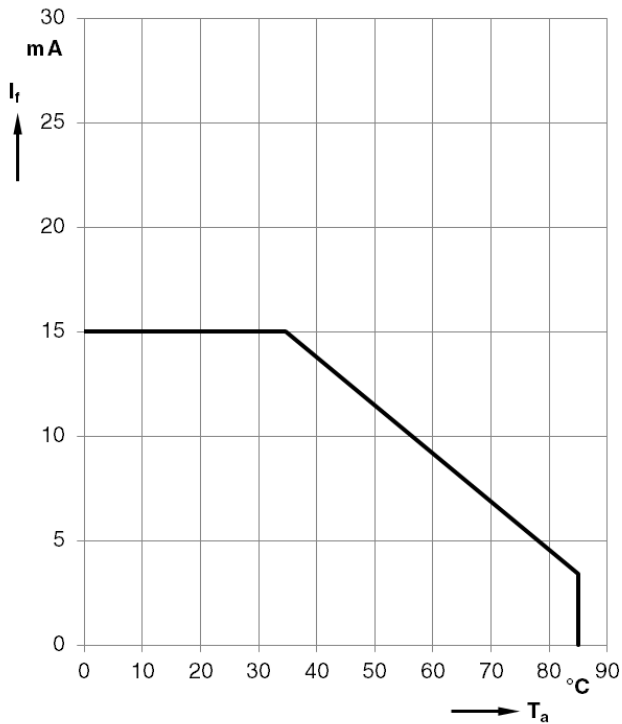
(single emitter) $I_F = f(t_p)$, $T_A = 85^\circ\text{C}$, duty cycle D



Diagrams for green emitters

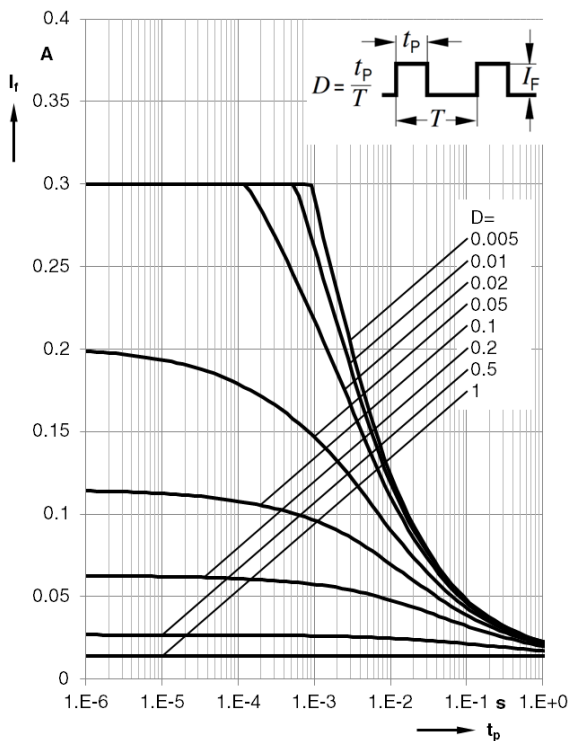
Max. permissible forward current ¹⁾

(three emitters) $I_{F,max} = f(T_A)$, $R_{thJA} = 800 \text{ K/W}$



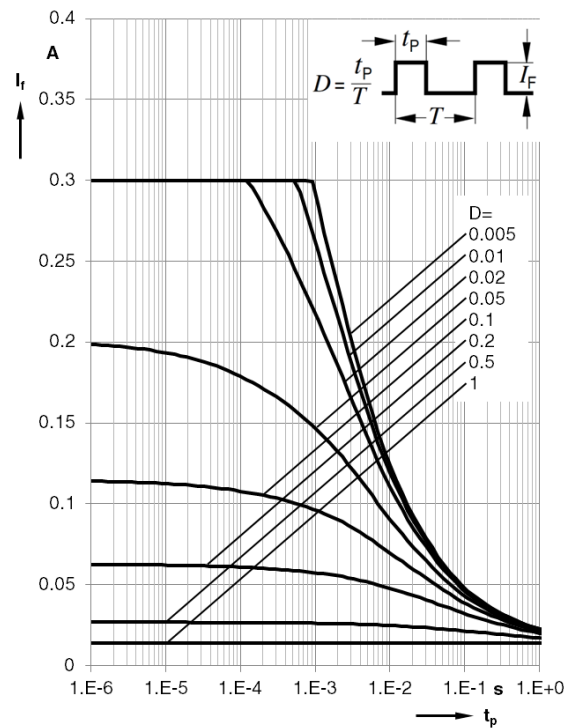
Permissible pulse handling capability ¹⁾

(three emitters) $I_F = f(t_p)$, $T_A = 40^\circ\text{C}$, duty cycle D



Permissible pulse handling capability ¹⁾

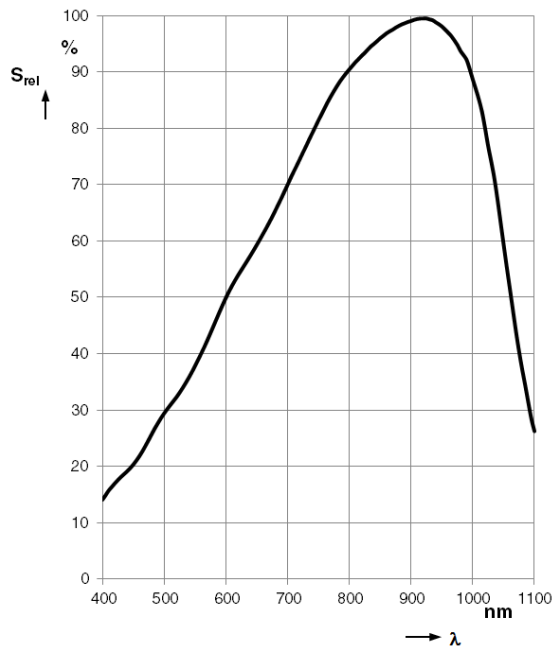
(three emitters) $I_F = f(t_p)$, $T_A = 85^\circ\text{C}$, duty cycle D



Diagrams for detector

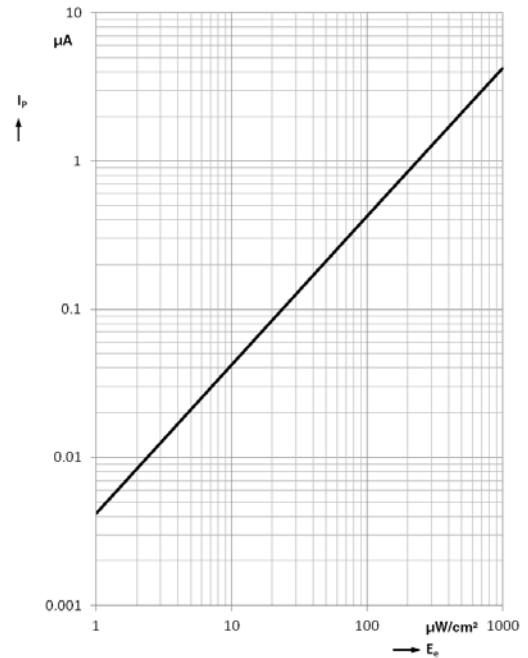
Relative spectral sensitivity ¹⁾

$S_{rel} = f(\lambda), T_A = 25\text{ °C}$



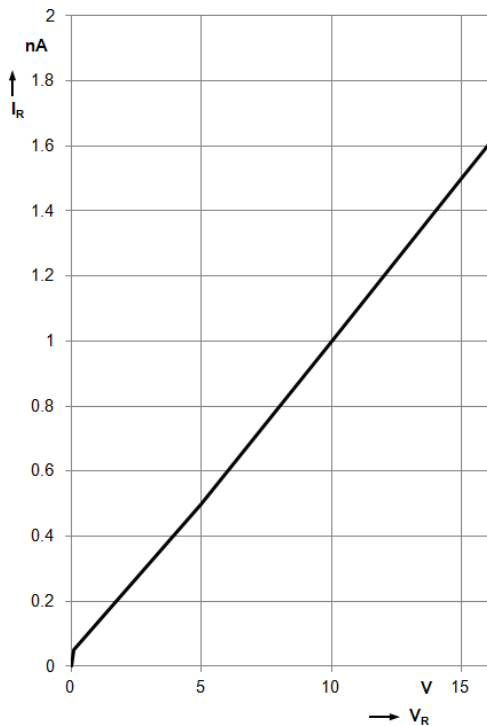
Photocurrent ¹⁾

$I_P(V_R = 5\text{ V}), \lambda = 530\text{ nm}, T_A = 25\text{ °C}$



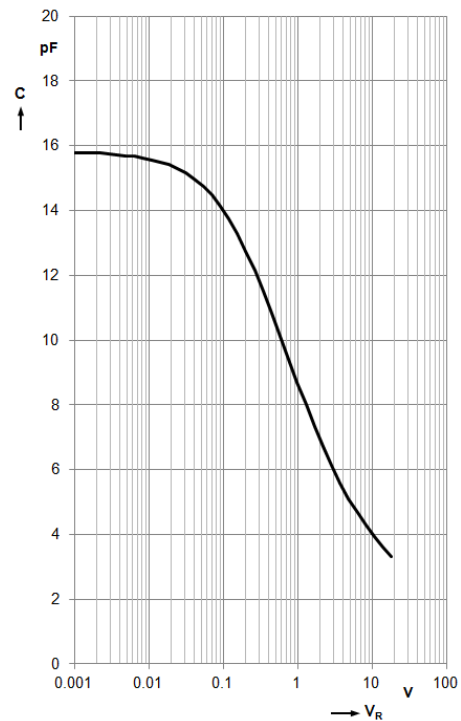
Dark current ¹⁾

$I_R = f(V_R), E = 0\text{ mW/cm}^2, T_A = 25\text{ °C}$



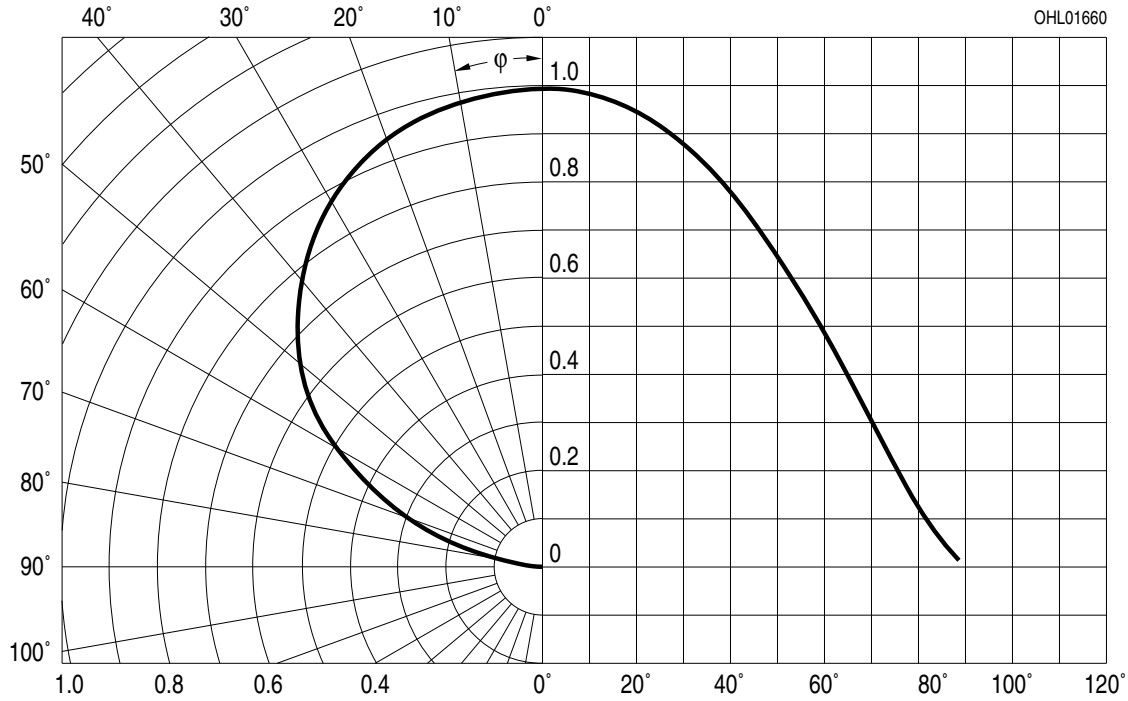
Capacitance ¹⁾

$C = f(V_R), f = 1\text{ MHz}, E = 0\text{ mW/cm}^2, T_A = 25\text{ °C}$



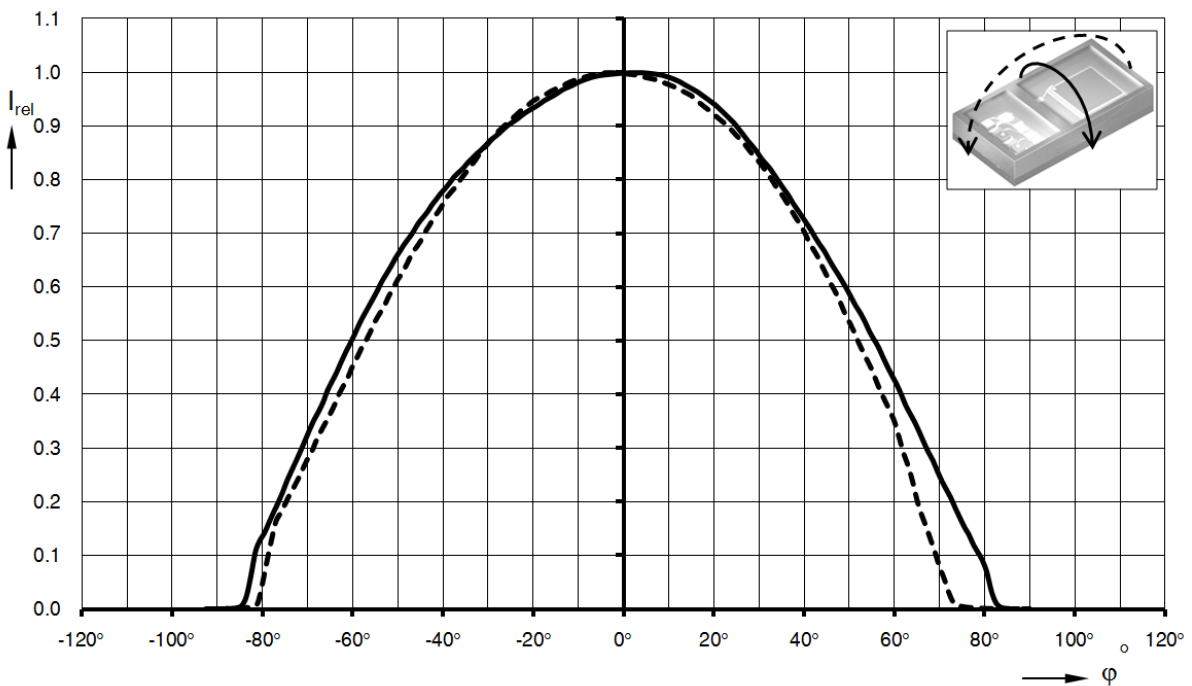
Directional characteristics of detector ¹⁾

$S_{rel} = f(\varphi)$

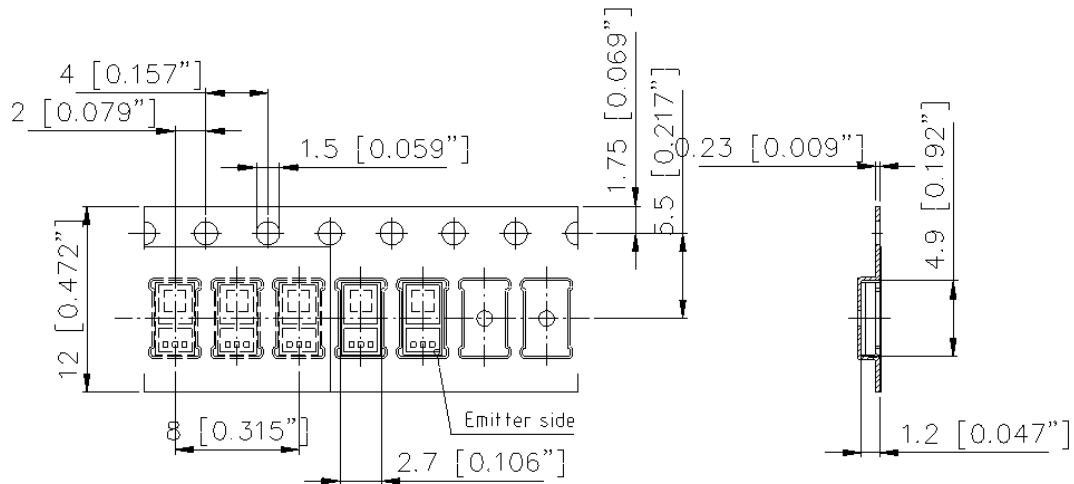


Radiation characteristics of emitter ¹⁾

$I_{rel} = f(\varphi)$

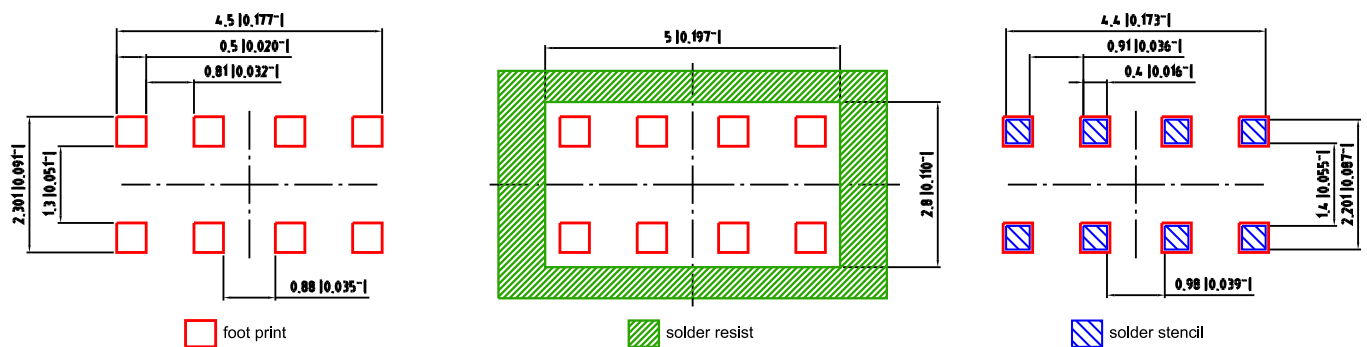


Method of Taping

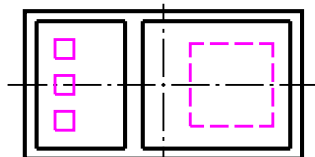


Dimensions in mm [inch]. / Maße in mm [inch].

Recommended solder pad design



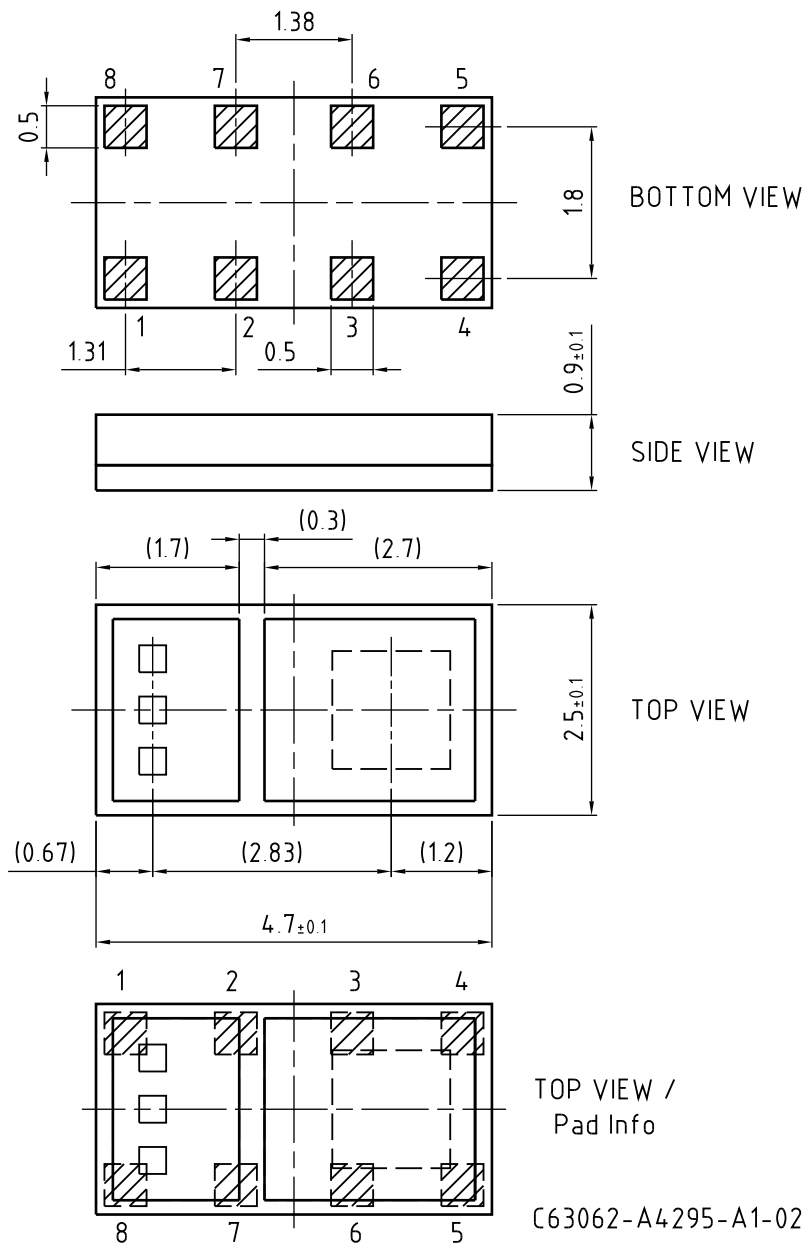
Component Location on Pad



Dimensions in mm (inch). / Maße in mm (inch).

E062.3010.172-01

Package Outline



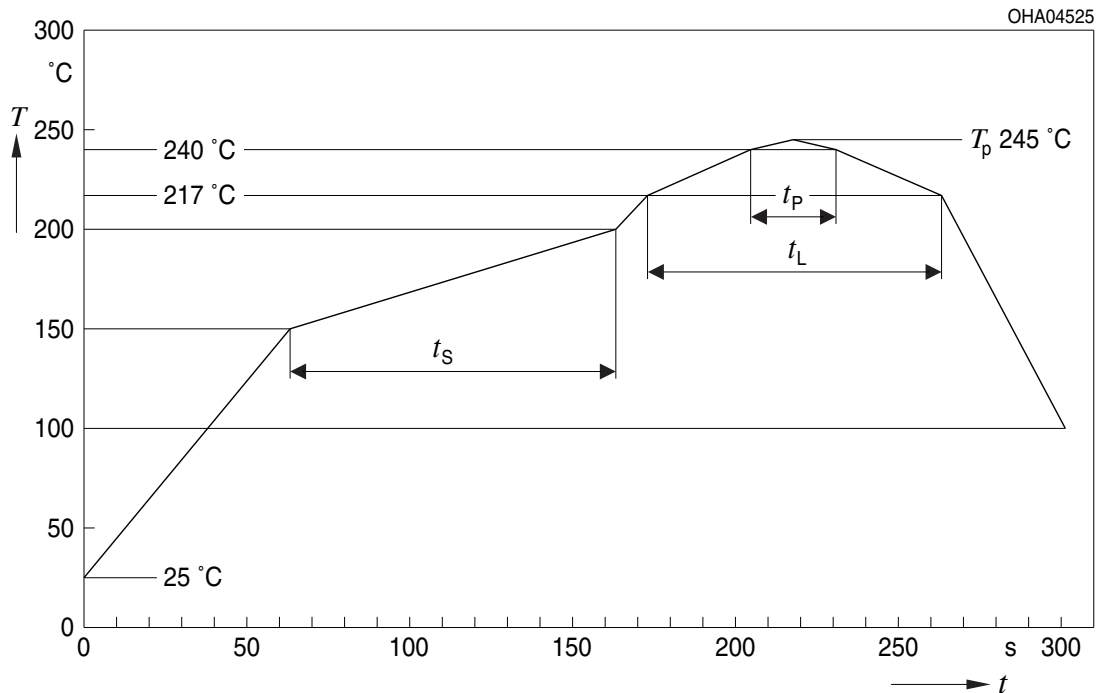
Pin1	Green LED 1 anode
Pin2	Green LED 1 cathode
Pin3	Green LED 2 cathode
Pin4	PD anode
Pin5	PD cathode
Pin6	Green LED 2 anode
Pin7	Green LED 3 cathode
Pin8	Green LED 3 anode

Dimensions in mm / Maße in mm.

Package: chip on board

Reflow Soldering Profile

Product complies to MSL Level 4 acc. to JEDEC J-STD-020D.01



OHA04612

Profile Feature Profil-Charakteristik	Symbol Symbol	Pb-Free (SnAgCu) Assembly			Unit Einheit
		Minimum	Recommendation	Maximum	
Ramp-up rate to preheat*) 25 °C to 150 °C			2	3	K/s
Time t_S T_{Smin} to T_{Smax}	t_S	60	100	120	s
Ramp-up rate to peak*) T_{Smax} to T_P			2	3	K/s
Liquidus temperature	T_L	217			°C
Time above liquidus temperature	t_L		80	100	s
Peak temperature	T_P		245	260	°C
Time within 5 °C of the specified peak temperature $T_P - 5$ K	t_P	10	20	30	s
Ramp-down rate* T_P to 100 °C			3	6	K/s
Time 25 °C to T_P				480	s

All temperatures refer to the center of the package, measured on the top of the component

* slope calculation DT/Dt : Dt max. 5 s; fulfillment for the whole T-range

Disclaimer

Language english will prevail in case of any discrepancies or deviations between the two language wordings.

Attention please!

The information describes the type of component and shall not be considered as assured characteristics.

Terms of delivery and rights to change design reserved.

Due to technical requirements components may contain dangerous substances.

For information on the types in question please contact our Sales Organization. If printed or downloaded, please find the latest version in the Internet.

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Critical components* may only be used in life-support devices** or systems with the express written approval of OSRAM OS.

*) A critical component is a component used in a life-support device or system whose failure can reasonably be expected to cause the failure of that life-support device or system, or to affect its safety or the effectiveness of that device or system.

**) Life support devices or systems are intended (a) to be implanted in the human body, or (b) to support and/or maintain and sustain human life. If they fail, it is reasonable to assume that the health and the life of the user may be endangered.

Disclaimer

Bei abweichenden Angaben im zweisprachigen Wortlaut haben die Angaben in englischer Sprache Vorrang.

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Glossary

1) **Typical Values:** Due to the special conditions of the manufacturing processes of LED and photodiodes, the typical data or calculated correlations of technical parameters can only reflect statistical figures. These do not necessarily correspond to the actual parameters of each single product, which could differ from the typical data and calculated correlations or the typical characteristic line. If requested, e.g. because of technical improvements, these typ. data will be changed without any further notice.

Glossar

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